

HSC277

Silicon Epitaxial Planar Diode for UHF/VHF tuner Band Switch

HITACHI

Rev. 0
Nov. 1995

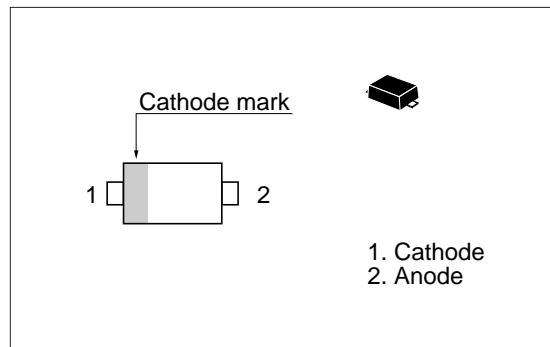
Features

- Low forward resistance. ($r_f=0.7\Omega$ max)
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Cathode Mark	Package Code
HSC277	Laser	UFP

Outline



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Junction temperature	T_j	125	°C
Power dissipation	P_d	150	mW
Operation temperature	T_{opr}	-20 to + 60	°C
Storage temperature	T_{stg}	-45 to +125	°C

Electrical Characteristics ($T_a = 25^\circ C$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	35	—	—	V	$I_R = 10 \mu A$
Reverse current	I_R	—	—	50	nA	$V_R = 25 V$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10 mA$
Capacitance	C	—	—	1.2	pF	$V_R = 6 V, f = 1 MHz$
Forward resistance	r_f	—	—	0.7	Ω	$I_F = 2 mA, f = 100 MHz$

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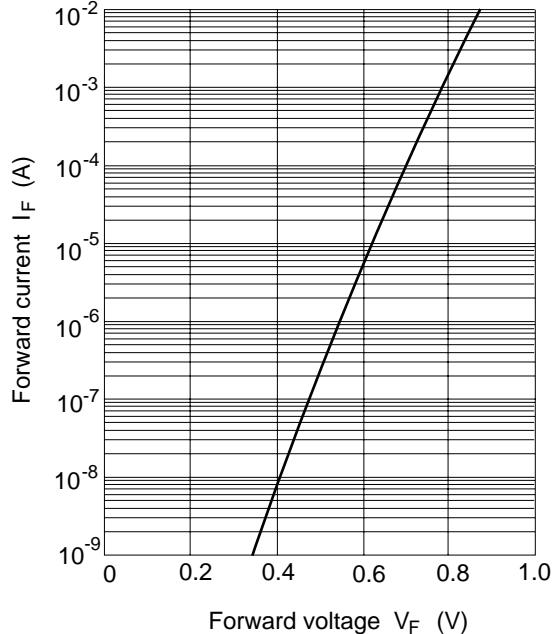


Fig.1 Forward current Vs.
Forward voltage

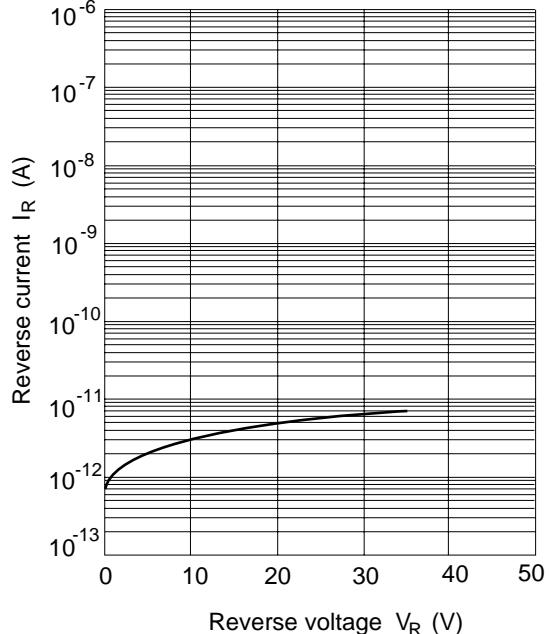


Fig.2 Reverse current Vs.
Reverse voltage

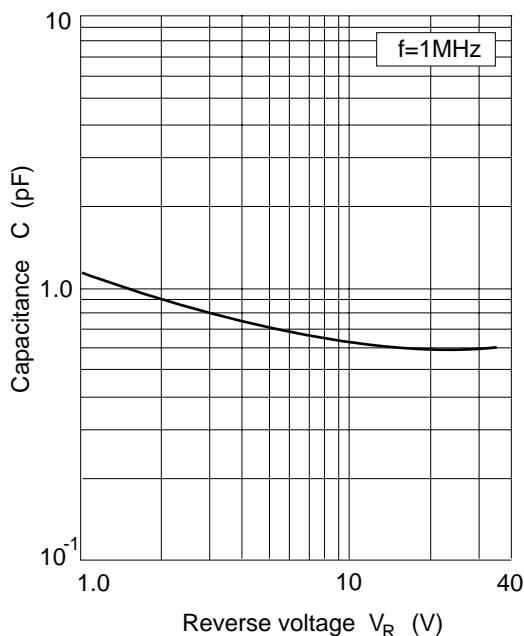


Fig.3 Capacitance Vs.
Reverse voltage

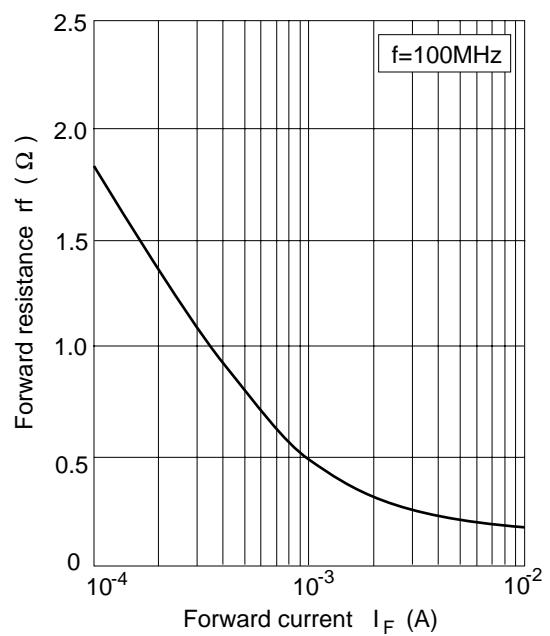


Fig.4 Forward resistance
Vs. Forward current

Package Dimensions

Unit: mm

